

AMENDMENTS TO THE CLAIMS:

Listing of claims:

This listing of claims replaces all prior versions and listings of claims in the application.

1. (Currently amended) A semiconductor device comprising:
 - a semiconductor element formed over a surface of a semiconductor substrate;
 - a first insulating film formed over the surface of the semiconductor substrate, the first insulating film covering the semiconductor element, and a top surface of the first insulating film being planarized;
 - a second insulating film formed over the first insulating film, the second insulating film having a dielectric constant lower than a dielectric constant of the first insulating film;
 - a first wiring pattern formed over the second insulating film; and
 - a conductive connection member buried in the second and first insulating films, the conductive connection member electrically interconnecting the first wiring pattern and the semiconductor element.

2. (Original) A semiconductor device according to claim 1, further comprising multilevel wiring patterns formed over the first wiring pattern, wherein the first wiring pattern and the multilevel wiring patterns are made of metal, and the first wiring pattern is disposed in a lowest level among wiring patterns made of metal.

3. (Original) A semiconductor device according to claim 1, wherein the second insulating film is made of organic insulating material or porous silica.

4. (Original) A semiconductor device according to claim 2, wherein the second insulating film is made of organic insulating material or porous silica.

5. (Original) A semiconductor device according to claim 1, wherein:

a surface modifying layer formed by using silane coupler or metal coupler is formed on an upper surface of the second insulating film;

the semiconductor device further comprises a third insulating film formed on the surface modifying layer and having a dielectric constant lower than the dielectric constant of the first insulating film; and

the first wiring pattern is buried in a trench whose bottom is defined by the surface modifying layer, the trench being formed in the third insulating film.

6. (Original) A semiconductor device according to claim 2, wherein:

a surface modifying layer formed by using silane coupler or metal coupler is formed on an upper surface of the second insulating film;

the semiconductor device further comprises a third insulating film formed on the surface modifying layer and having a dielectric constant lower than the dielectric constant of the first insulating film; and

the first wiring pattern is buried in a trench whose bottom is defined by the surface modifying layer, the trench being formed in the third insulating film.

7. (Original) A semiconductor device according to claim 3, wherein:

a surface modifying layer formed by using silane coupler or metal coupler is formed on an upper surface of the second insulating film;

the semiconductor device further comprises a third insulating film formed on the surface modifying layer and having a dielectric constant lower than the dielectric constant of the first insulating film; and

the first wiring pattern is buried in a trench whose bottom is defined by the surface modifying layer, the trench being formed in the third insulating film.

8. (Currently amended) A semiconductor device comprising:

a semiconductor element formed over a surface of a semiconductor substrate;

a protective film formed over the surface of the semiconductor substrate, the protective film covering the semiconductor element, the protective film having a planarized surface;

a low dielectric constant film formed over the protective film, the low dielectric constant film having a dielectric constant lower than a dielectric constant of the protective film and made of porous silica or organic insulating material;

a first wiring pattern formed over or above the low dielectric constant film; and

a conductive connection member buried in the low dielectric constant film and the protective film, the conductive connection member electrically interconnecting the first wiring pattern and the semiconductor element.

9. (Currently amended) A method of manufacturing a semiconductor device comprising steps of:

(a) forming a semiconductor element over a surface of a semiconductor substrate;

(b) forming a ~~protective~~ first insulating film made of insulating material over the surface of the semiconductor substrate by a vapor deposition method, the protective film covering the semiconductor element;

(b1) planarizing a surface of the first insulating film;

(c) forming a ~~first~~ second insulating film over the ~~protective~~ first insulating film by a coating method, the ~~first~~ second insulating film being made of insulating material having a lower dielectric constant than the ~~prototype~~ first insulating film;

(d) forming a via hole through the ~~first~~ second insulating film and the ~~protective~~ first insulating film;

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(e) burying a conductive plug in the via hole; and

(f) forming a metal wiring pattern over the ~~first~~ second, insulating film, the metal wiring pattern being connected to the conductive plug.

10. (Original) A method of manufacturing a semiconductor device according to claim 9, further comprising after the step (c):

a step of forming a second insulating film made of insulating material over the first insulating film by a vapor deposition method; and

a step of planarizing a surface of the second insulating film,

wherein in the step (d) the via hole is formed extending also through the second insulating film.